

Indications for a line of continuous phase transitions at finite temperatures connected with the apparent metal-insulator transition in 2d disordered systems

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Abstract

In a recent experiment, Lai *et al.* [Phys. Rev. B **75** (2007) 033314] studied the apparent metal-insulator transition (MIT) of a Si quantum well structure. Tuning the charge carrier concentration n , they measured the conductivity $\sigma(T, n)$ for a very dense set of n values. They observed linear T dependences of σ around the Fermi temperature and found that the corresponding $T \rightarrow 0$ extrapolation $\sigma_0(n)$ exhibits a sharp bend just at the MIT. Reconsidering the data by Lai *et al.*, it is shown here that this sharp bend is related to a peculiarity of $\sigma(T = \text{const.}, n)$, which is clearly detectable in the whole T range up to 4 K, the highest measuring temperature in that work. It may indicate a sharp continuous phase transition between the regions of apparent metallic and activated conduction to be present at finite temperature. This interpretation is confirmed by a scaling analysis without fit, which illuminates similarities to previous experiments and provides understanding of the shape of the peculiarity and of sharp peaks found in $d \log_{10} \sigma / d n(n)$. Simultaneously, the scaling analysis uncovers a strange feature of the apparent metallic state.

Key words: Metal-insulator transition, localisation, scaling, apparent metallic phase

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1. Introduction

Is electronic transport in 2-dimensional (2d) disordered systems exclusively nonmetallic, so that the resistivity $\rho(T)$ always diverges as the temperature T tends to 0, or can it also have metallic character? This fundamental problem has been controversially debated for three decades: The existence of a corresponding metal-insulator transition (MIT) was denied by the localisation theory of Abrahams *et al.* [1], which, however, neglects electron-electron interaction. Thus, it came as a surprise when Kravchenko *et al.*, who had varied the charge carrier concentration n in high mobility MOSFET samples, first reported a strong decrease of ρ down to 20 mK [2]. They considered the conduction in the respective (T, n) region as metallic, an interpretation which was questioned in particular by Altshuler and Maslov [3]. The nature of the apparent metallic state has remained puzzling up to now, for recent reviews see Refs. [4, 5].

Recently, Lai and coworkers studied the transport properties close to the apparent MIT of an n-type Si quantum well confined in a $\text{Si}_{0.75}\text{Ge}_{0.25}/\text{Si}/\text{Si}_{0.75}\text{Ge}_{0.25}$ heterostructure [6]. The authors observed the conductivity σ to have nearly linear T dependences around the Fermi temperature T_F varying between 2 and 2.5 K. They showed that $\sigma_0(n)$, the $T = 0$ conductivity obtained by linear extrapolation from this T region, exhibits two regimes of different slope. Particularly important, there is a sharp bend at the transition between the two regimes. It coincides with the n value, n_c , where $d\sigma/dT$ changes its sign as

$T \rightarrow 0$. The authors interpret this finding as an indication of the existence of two different phases. Thus, the apparent MIT should be related to a real phase transition at $T = 0$. This transition is commonly expected to be smoothed out at finite T .

However, such a smoothing is not a must for a quantum phase transition as is obvious from two examples: The Ising ferromagnet LiHoF_4 in transverse magnetic field undergoes a quantum phase transition at $T = 0$, where the quantum critical point is the beginning of a line of continuous phase transitions at finite T [7]. The phase diagram of the quasi-two-dimensional organic conductor $\kappa\text{-(BEDT-TTF)}_2\text{X}$ exhibits a line of first-order transitions at finite T separating an antiferromagnetic-insulator phase from an unconventional-superconductor phase at low T [8].

From this perspective, the additional observation by Lai *et al.*, that the slope of $\sigma(T)$ for $T \sim T_F$ is almost constant close to the MIT, $n = n_c$, provokes two interesting questions: (i) Provided the extrapolated $\sigma_0(n)$ has a knee indeed, and the slope used in extrapolation is roughly constant, should not $\sigma(T = \text{const.}, n)$ exhibit a knee at n_c also for finite T ? (ii) If yes, is the existence of this peculiarity restricted to the region of linear $\sigma(T)$ around T_F , or is it a more general phenomenon?

Starting from these questions, the present work points to several indications for the MIT in 2d systems being connected with a line of continuous phase transitions at finite T . It substantially extends the detailed arguments given in Ref. [9]: More data are taken into consideration in the scaling region, where $\sigma(T, n) = \sigma((n - n_c)/T^{1/\beta})$, consequences of this scaling for the physical nature of the apparent metallic state are discussed, and possible corresponding similarities with the transport in an

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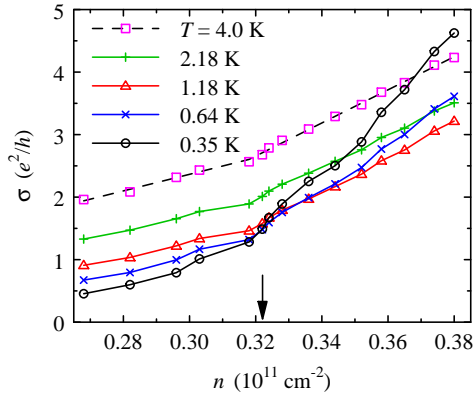


Figure 1: Charge carrier concentration dependence of the conductivity for the Si quantum well structure studied in Ref. [6]. Data were obtained from Fig. 1(b) of that work. The arrow marks the critical concentration n_c of the apparent MIT, see text. The dashed line is a fit by the piecewise linear function introduced in the text. The full lines serve as guide to the eyes.

AlAs quantum well [10] are illuminated.

2. Phenomenological reconsideration of the experiment by Lai and coworkers

To find out to which extent and in which form the sharp bend of $\sigma_0(n)$ persists when T is finite, I digitised the high-resolution preprint version of Fig. 1(b) of Ref. [6]. Fig. 1 depicts the obtained $\sigma(T = \text{const.}, n)$ data for five T values. First of all, this graph shows that all $\sigma(T = \text{const.}, n)$ curves share a peculiar feature, namely an “indentation” at $n \approx 0.32 \cdot 10^{11} \text{ cm}^{-2}$. It occurs close to the concentration value where $d\sigma/dT$ changes its sign at the lowest T considered in Ref. [6]. This value, $n_c = 0.322 \cdot 10^{11} \text{ cm}^{-2}$, is the critical concentration of the apparent MIT. It is marked by arrows in Figs. 1, 2, and 4.

To answer the question whether or not the sharp bend observed by Lai *et al.* at $\sigma_0(n)$ persists at finite T , fits by the piecewise linear function $f_{\text{plf}}(n) = a + bn + c(n - n_k)\theta(n - n_k)$ with the adjustable parameters a , b , c , and n_k were tried. Here, n_k denotes the knee position, and θ stands for the Heaviside step function. For comparison, the data sets were approximated by polynomials of third order, which have the same number of adjustable parameters. Additionally to the data shown in Fig. 1, $\sigma(0.47\text{K}, n)$ and $\sigma(0.87\text{K}, n)$ were included in this analysis.

Table 1, left part, presents the optimum knee positions n_k and the related values of the least square sum χ^2 , where weight 1 was ascribed to all points. It is remarkable that the same n_k value, $0.318 \cdot 10^{11} \text{ cm}^{-2}$, results for all temperatures but 0.47 and 0.35 K. This n_k value is only very slightly lower than the abscissa of the knee for the $T \rightarrow 0$ extrapolation $\sigma_0(n)$ in Fig. 2 of Ref. [6]. Moreover, note that, for the four highest T values, piecewise linear functions approximate the experimental data clearly better than the polynomials.

The advantage of piecewise linear functions over polynomials of third order diminishes with decreasing T . This trend

Table 1: Results of phenomenological fits of $\sigma(T = \text{const.}, n)$ data from the Si quantum well study Ref. [6]. Piecewise linear functions (plf) and polynomials of third order (pto) are compared. Values of knee positions n_k and least square sums χ^2 are given in units of 10^{11} cm^{-2} and e^4/h^2 , respectively. The left group of columns results from consideration of the complete data sets, the right group is obtained from the data points fulfilling $0.5\sigma(T, n_c) < \sigma(T, n) < 2.0\sigma(T, n_c)$. N denotes the number of data points taken into account.

$T(\text{K})$	complete data set				restricted data set			
	N	n_k	χ_{plf}^2	χ_{pto}^2	N	n_k	χ_{plf}^2	χ_{pto}^2
4.0	15	0.318	0.010	0.024	15	0.318	0.010	0.024
2.18	15	0.318	0.006	0.019	15	0.318	0.006	0.019
1.18	15	0.318	0.010	0.019	14	0.318	0.009	0.018
0.87	15	0.318	0.016	0.023	13	0.318	0.009	0.020
0.64	15	0.318	0.028	0.031	11	0.318	0.013	0.026
0.47	15	0.316	0.061	0.050	9	0.318	0.023	0.032
0.35	15	0.315	0.097	0.063	9	0.318	0.024	0.036

is not surprising because, in the region of activated conduction, $\sigma(T = \text{const.}, n)$ vanishes in some exponential way with decreasing n . Hence, when considering a fixed n range and lowering T , the σ region broadens, and the basic nonlinearity gets increasing weight compared to the “indentation” at $n \approx 0.32 \cdot 10^{11} \text{ cm}^{-2}$. Thus, a more meaningful comparison of both approximations is obtained restricting all fits to comparable σ intervals, here to $\{0.5\sigma(T, n_c), 2.0\sigma(T, n_c)\}$. Under this condition, for each of the T values considered, piecewise linear functions approximate the data clearly better than polynomials of third order, see Tab. 1, right part. Moreover, now all fits yield the same n_k value, $0.318 \cdot 10^{11} \text{ cm}^{-2}$.

Thus, for all T values, some characteristic change occurs within a very small n region close to the knee of the piecewise linear fit. In this sense, the sharp bend observed by Lai *et al.* at the $T \rightarrow 0$ extrapolation $\sigma_0(n)$ turns out to be not smoothed for finite T . In particular, it seems to exist even for $T \ll T_F$, where $\sigma(T, n = \text{const.})$ is nonlinear and considerably deviates from the linear extrapolation estimate from the vicinity of T_F . Because $n_k \approx n_c$ for all T , it is likely that the bends originate from sharp continuous phase transitions separating the regions of apparent metallic and activated conduction at finite T .

However, there is a tiny systematic difference between the values of n_k and n_c . It presumably arises from the approximation by piecewise linear functions being an oversimplification. This aspect is considered in the next section.

3. Scaling analysis

Provided the sharp bend is indeed related to a phase transition, how may it arise? What fine structure could it have? On a macroscopic level, $\sigma(T, n)$ can be described in the following way. Suppose, on the insulating side of the apparent MIT, the T dependence of σ scales as observed by Kravchenko *et al.* [11] at the resistivity of MOSFETs,

$$\sigma(T, n) = \sigma(t) \quad \text{with} \quad t = T/T_0(n). \quad (1)$$

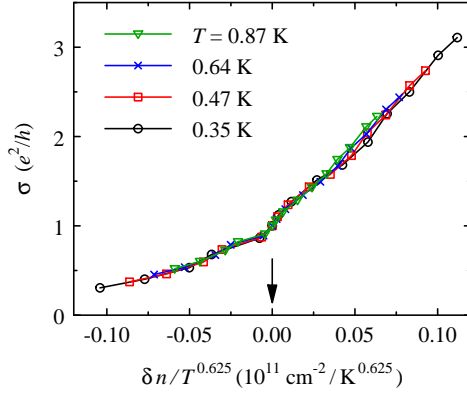


Figure 2: Scaling check without adjustment of parameters considering the four $\sigma(T = \text{const}, n)$ data sets with $T < 1\text{K}$ which are analysed in Tab. 1.

For further references on scaling of T dependences close to the MIT in various 2d and 3d systems, see [9]. Assume that this scaling holds up to n_c where $T_0(n) \rightarrow 0$. Suppose furthermore

$$T_0(n) = A|\delta n|^\beta \quad \text{with} \quad \delta n = n - n_c, \quad (2)$$

where A is a constant, which might, however, be sample dependent. Thus, σ should depend only on the quotient $T/|\delta n|^\beta$ or rather on $\delta n/T^{1/\beta}$, compare Fig. 10 of Ref. [11].

The value of the critical exponent β should be universal. It was determined by Kravchenko *et al.* [11] from their MOSFET experiment, $\beta = 1.6 \pm 0.1$. The value $n_c = 0.322 \cdot 10^{11} \text{ cm}^{-2}$ is known from the sign change of $d\sigma/dT$ as $T \rightarrow 0$. Thus, without adjusting any parameter, a scaling check of $\sigma(T, n)$ can be performed plotting σ as function of $\delta n/T^{1/\beta}$ for different T . This is done in Fig. 2 considering the $\sigma(T = \text{const}, n)$ data sets for $T = 0.35, 0.47, 0.64$, and 0.87 K . Data sets for higher T are not taken into account since $\sigma(T, n_c)$ becomes T dependent above roughly 1 K , presumably because some additional mechanism becomes relevant there, see Fig. 1 of Ref. [6].

Note that such a scaling check ascribes higher weight to the points more distant from n_c , while the analysis in the previous section is particular sensitive with respect to the data very close to n_c . Therefore, here, the influence of sample inhomogeneities is reduced in comparison to the fits in Tab. 1.

Figure 2 shows that, for $n < n_c$, all four $\sigma(\delta n/T^{0.625})$ curves nicely fall together although no parameter has been adjusted. It is unlikely that the agreement of the curves arises only by chance, so that Fig. 2 can be considered as support of the scaling hypothesis. Hence, since $T_0(n) \rightarrow 0$ as $n \rightarrow n_c$, this graph indirectly indicates phase transitions at finite T .

Also for $n > n_c$, that means within the apparent metallic phase, the four curves in Fig. 2 collapse. This is surprising: In case of conventional metallic conduction, as T vanishes, $\sigma(T, n)$ would tend to a finite and n dependent value, $\sigma(0, n)$, which increases monotonously with n . Vanishing T corresponds to diverging $\delta n/T^{0.625}$, so that curves, which were drawn for varying T and fixed δn in Fig. 2, would split, in contradiction to the observed scaling. Thus, scaling for $n > n_c$ cannot be understood

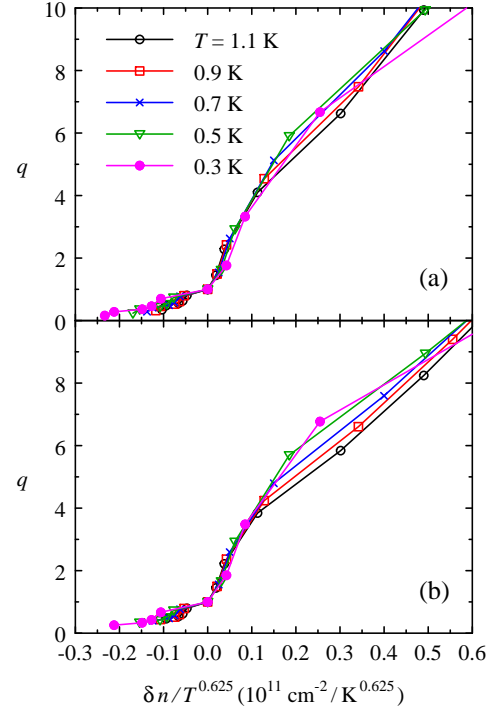


Figure 3: Scaling check for AlAs quantum well data from Fig. 2 of Ref. [10]: (a) high-mobility and (b) low-mobility directions. Here, $n_c = 0.70 \cdot 10^{11} \text{ cm}^{-2}$ is presumed, see text.

in terms of conventional metallic behaviour. Superconductivity at $T = 0$ might be an alternative, compare the discussion in Ref. [11] and the study of ultrathin Bi films by Liu *et al.* [12].

However, for $n > n_c$, a lot of publications have reported saturation of σ as $T \rightarrow 0$. Thus several questions arise: Might the scaling observed here be restricted to the considered material or to a tight vicinity of n_c ? What about the influence of inhomogeneities, sample size or thermal decoupling?

To get a preliminary answer to the first question, reconsider now an experimental study of an AlAs quantum well by Papadakis and Shayegan [10]. Figure 3 shows scaling checks for data obtained by digitising Fig. 2 of Ref. [10]. To correct for the T dependence of σ at n_c , the quotient $q(T, n) = \sigma(T, n)/\sigma(T, n_c)$ is considered here instead of $\sigma(T, n)$ itself. This approach turned out to be effective for the Si quantum well data by Lai *et al.* in Ref. [9].

The scaling check given in Fig. 3 has a hidden parameter: Contrary to the situation in Fig. 2, the n_c value has some uncertainty. According to Fig. 2 of Ref. [10], the n_c values defined by $d\sigma/dT = 0$ as $T \rightarrow 0$ are roughly 0.65 and $0.70 \cdot 10^{11} \text{ cm}^{-2}$ for the high- and low-mobility directions, respectively, but n_c should be uniquely defined. (A possible origin of the direction dependence of the mobility is discussed in detail in Ref. [10].) In comparing plots for several values of n_c , the best data collapse was observed for $n_c = 0.70 \cdot 10^{11} \text{ cm}^{-2}$.

Figure 3 (broader n range) resembles Fig. 2 to a large extent. Thus, although the random dispersion of the data points is here clearly higher than in Fig. 2, the proposed scaling approach

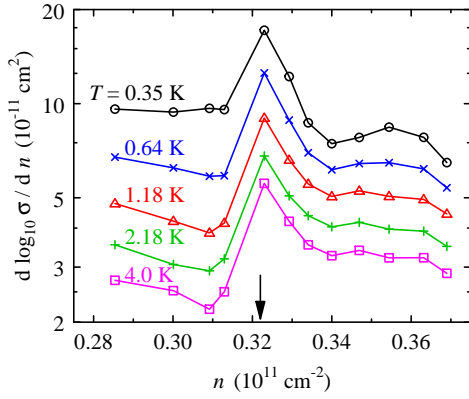


Figure 4: $d \log_{10} \sigma / d n$ versus n for the Si quantum well curves displayed in Fig. 1. Concerning details of the calculation of the derivative values see Ref. [9].

might be applicable to the AIAs data from Ref. [10]. Moreover, also in Fig. 3, the slope changes significantly at $n = n_c$.

Turn now again to the analysis of the Si quantum well data by Lai *et al.* The “indentation” around $\delta n = 0$ in Fig. 2 can be understood in the following way. Since $T_0(n) \rightarrow 0$ and $t \rightarrow \infty$ as $n \rightarrow n_c$ for arbitrary constant T , the ansatz

$$\sigma(t) = \sigma_c \cdot (1 - B t^{-\nu}) \quad (3)$$

is suggested. Here B is a dimensionless constant and ν a positive exponent. Hence,

$$\sigma(T, n) = \sigma_c \cdot (1 - C |\delta n|^{\beta\nu}) \quad \text{with} \quad C = B(A/T)^\nu. \quad (4)$$

Only a rough guess of the value of ν can be given at present. In case of hopping in the Coulomb gap for small t , ν would be $1/2$. However, according to Ref. [11], ν may be expected to be smaller for large t . In both cases, the product $\beta\nu$ would be clearly smaller than 1 so that $\sigma(T = \text{const.}, n)$ should have a root-like peculiarity at n_c .

This hypothetical peculiarity implies a divergence of $d\sigma/dn$, and thus also of $d \log_{10} \sigma / d n$. Already at finite temperature, it indicates the transition between activated and apparent metallic conduction. As a consequence, it permits the precise identification of the MIT. This approach resembles the strategy used in studying ultrathin metal films in Ref. [13], where the crossover between logarithmic and exponential temperature dependence was related to a change in the thickness dependence of the thickness derivative of the conductance.

In reality, the expected divergence would be smoothed to a sharp maximum. Fig. 3 shows that, indeed, $d \log_{10} \sigma / d n$ exhibits such a sharp peak independent of T – note that a logarithmic scale is used to display the derivative values. It is striking, although a natural consequence of Eq. (4), that the peak is always located just at n_c , another indication of a phase transition occurring at finite T . Of course, the question arises whether or not this sharp maximum is specific to the Si quantum well studied in Ref. [6]. The comparison of Fig. 2 with Fig. 3 suggests that also the AIAs quantum well studied in Ref. [10] may exhibit such a feature.

4. Challenges

As a whole, the presented indications give strong support to the hypothesis that the MIT at $T = 0$ is connected with a line of sharp phase transitions at finite T . However, this conclusion has to be confirmed by further experiments. Such studies should primarily focus on enhancing precision, in particular concerning homogeneity of the samples, rather than on reducing the lowest accessible T for the following reasons: In plots analogous to Fig. 2, the effect of inhomogeneities increases with decreasing T . For arbitrary T , inhomogeneities smooth the indentations shown in Figs. 1 to 3 and the peaks in Fig. 4.

In case, the hypothetical line of phase transitions at finite T exists indeed, three questions arise: Does it terminate at a certain T value? Under which conditions does scaling hold in the region of apparent metallic conduction, is there a specific (T, n) region? What is the nature of the related unconventional phase?

I am indebted to T. Vojta for an important literature hint.

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